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RoHS Compliant

NPN 3. COLLECTOR

1. EMITTER

2. BASE

Absolute Maximum Ratings

Description	Symbol	Value	Unit
Collector Emitter Voltage, $R_{BE} \le 10\Omega$	Vcer	50	V
Collector Base Voltage	Vсво	75	V
Emitter Base Voltage	Vebo	7	V
Power Dissipation at T _A = 25°C Derate above 25°C	PD	800 4.57	mW mW/°C
Power Dissipation at Tc = 25°C Derate Above 25°C	PD	3 17.15	W mW/°C
Operating and Storage Junction Temperature Range	Tj, Tstg	- 65 to +200	°C

Electrical Characteristics: (T_A = +25°C Unless otherwise specified)

Description	Symbol	Test Conditions	Min	Мах	Unit
Collector Emitter Voltage	VCER	lc = 1mA, R _{BE} ≤ 10Ω	50		V
Collector Base Voltage	Vсво	Ic = 100μA, Iε = 0	75		V
Emitter Base Voltage	Vebo	Iε = 100μA, Ic = 0	7		V
Collector Cutoff Current	Ісво	Vcb = 60V, Ie = 0 Vcb = 60V, Ie = 0, Ta = 150°C		10 10	nA µA
Emitter Cutoff Current	Іево	VEB =5V, IC = 0		5	nA
DC Current Gain	hfe	Ic = 0.01mA, Vce = 10V Ic = 0.1mA, Vce =10V Ic = 10mA, Vce =10V Ic=10mA, Vce=10V, Ta= -55°C Ic = 150mA, Vce = 10V Ic = 150mA, Vce = 10V	20 35 75 35 100 40	300	
Collector Emitter Saturation Voltage	*VCE(Sat)	Ic = 150mA, Iв = 15mA		0.5	V
Base Emitter Saturation Voltage	*VBE(Sat)	Ic = 150mA, Iв = 15mA		1.3	V

Small Signal Characteristics

Description	Symbol	Test Conditions	Min	Max	Unit
Transition Frequency	f⊤	Ic=50mA, Vc==10V, f=20MHz	70		MHz
Output Capacitance	Cob	Vcb = 10V, IE = 0, f = 100kHz		25	pF
Input Capacitance	Cib	V _{EB} = 0.5V, Ic = 0, f = 100kHz		80	рF

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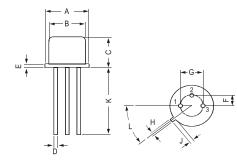
NPN Silicon Planar Transistor 50VCE0

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Description	Symbol	Test Conditions	Min	Мах	Unit
Input Impedance	hib	Ic = 1mA, Vcв = 5V, f = 1kHz Ic = 5mA, Vcв = 10V, f = 1kHz	24 4	34 8	Ω Ω
Voltage Feedback Ratio	hrb	Ic = 1mA, Vсв = 5V, f = 1kHz Ic = 5mA, Vсв = 10V, f = 1kHz		5 5	x10 ⁻⁴ x10 ⁻⁴
Small Signal Current Gain	h _{fe}	Ic = 1mA, Vcв = 5V, f = 1kHz Ic = 5mA, Vcв = 10V, f = 1kHz	50 70	200 300	
Output Admittance	hob	Ic = 1mA, Vcв = 5V, f = 1kHz Ic = 5mA, Vcв = 10V, f = 1kHz	0.05 0.05	0.05 0.05	µmhos µmhos
Noise Figure	NF	Ic = 300mA, Vce = 10V, f = 1kHz		8	dB

*Pulse Test: Pulse Width \leq 300µs, Duty Cycle < 2%

TO-39 Metal Can Package



Dim.	Min.	Max.
А	8.5	9.39
В	7.74	8.50
С	6.09	6.60
D	0.4	0.53
E	-	0.88
F	2.41	2.66

Dim.	Min.	Max.
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
К	12.7	-
L	42 Deg.	48 Deg.

Dimensions : Millimetres

Part Number Table

Description	Part Number	
NPN Silicon Planar Transistor, 50V, TO-39	MP001165	

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